

## SUBJECT TEACHING GUIDE

G992 - Electronic Devices and Circuits

Degree in Industrial Electronic Engineering and Automatic Control Systems

Academic year 2019-2020

1. IDENTIFYING DATA					
Degree	Degree in Industrial Electronic Engineering and Automatic Control Systems			Type and Year	Compulsory. Year 2
Faculty	School of Industrial Engineering and Telecommunications				
Discipline	Subject Area: Electronics and Automation Module in Common with the Industrial Branch				
Course unit title and code	G992 - Electronic Devices and Circuits				
Number of ECTS credits allocated	6	Term	Semester based (2)		
Web					
Language of instruction	Spanish	English Friendly	Yes	Mode of delivery	Face-to-face

Department	DPTO. TECNOLOGIA ELECTRONICA E INGENIERIA DE SISTEMAS Y AUTOMATICA
Name of lecturer	FRANCISCO JAVIER AZCONDO SANCHEZ
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Other lecturers	MARIA DEL MAR MARTINEZ SOLORZANO JUAN ECHEVARRIA CUENCA YOLANDA LECHUGA SOLAEGUI FRANCISCO JAVIER DIAZ RODRIGUEZ

### 3.1 LEARNING OUTCOMES

- Students are equipped with the following skills:
  - Simulation and use of electronic devices
  - Design of basic analog and digital electronic circuits
  - Characterization of power switch devices.
  - Circuit building and test
  - Use of electronic instruments
- Students understand the following topics
  - Diodes, MOSFETs and BJTs operation principles
  - Design and analysis of single-stage amplifiers using MOSFETs and BJTs
  - Design and analysis of basic digital circuits using MOSFETs
  - Operation principles of power switches in power conversion stages

### 4. OBJECTIVES

- Understand the operating principles of Diodes, MOSFETs and BJTs
- Understand the design principles and analysis of single-stage amplifiers using MOSFETs and BJTs
- Understand the operation principles of a power switch device in power conversion stages
- Understand the design and analysis principles of digital circuits built with MOSFET transistors

## 6. COURSE ORGANIZATION

### CONTENTS

1	<p>Block 1. Circuits with diodes</p> <p>1.1. Diodes and optoelectronic devices fundamentals. Semiconductors (Energy bands, electrons and holes; Intrinsic and doped semiconductors. Generation and recombination of charge carriers; Conduction mechanisms: Diffusion and Drift. P-N junction: Structure, inverse and direct bias, I - V characteristic. Temperature effects. Drift zone in power device. Conductivity modulation. Other diode types: Varactor, Schottky, Photodiode, LED, Solar Cell.</p> <p>1.2.- Diode models. V-I characteristic of the p-n junction. Ideal diode. Constant voltage drop model. Voltage source + resistor model. Small-signal model. Zener model. Diode SPICE model.</p> <p>1.3.- Applications of diodes. Battery charger. Half and Full Wave rectifiers. Bridge rectifier. Peak voltage detector. Voltage stabilizer. Effect of the load on the output voltage. Demodulator. Clamp voltage circuits. Piece-wise linear transfer functions. Diode circuit analysis with SPICE.</p>
2	<p>Block 2. Circuits with MOS transistors</p> <p>2.1. MOS devices. MOS transistor structure. V-I characteristics. Operation in the linear or triode area. Operation in the saturation area. MOS capacitances. Large-signal model. Small-signal model. PMOS transistors. SPICE model</p> <p>2.2. MOS transistor in steady-state operation. MOS transistor bias. Resistor divider. Self-bias. Design with integrated circuit technology. NMOS inverters. Enhancement-type MOS. Depletion-type MOS. Current source mode. Current mirrors. Current mirror with cascode stage.</p> <p>2.3. MOS transistor in digital circuits. Static characteristics of a digital inverter. NMOS and CMOS digital inverters. Voltage transfer function. Supply current. MOS switches. Dynamic characteristic of a digital inverter. Propagation time. Power dissipation. NMOS and CMOS logic gates.</p> <p>2.4. Single and multi-stage MOS amplifiers. Amplification concept. Voltage gain. Input and output resistance. Small-signal model. Single-stage discrete MOS amplifier. Active loads technique. Common source, common drain, and common gate configurations. Cascode amplifier. Multi-transistors coupling. Multi-stage amplifier. SPICE simulation examples.</p> <p>2.5. The MOS differential amplifier. MOS differential pair. Large-signal operation. Small-signal operation. Common-mode gain. Differential-mode gain. Common-mode rejection ratio (CMRR). Non-ideal characteristics of the differential amplifiers. Differential amplifier with active loads. Differential input to output conversion.</p> <p>2.6. MOS integrated circuits manufacturing. Introduction. Integrated circuit manufacturing steps. VSLI process to obtain integrated devices: MOSFET, Resistors, Capacitors, Inductors, Diodes and Bipolar transistors. CMOS Integrated circuit mask and layout design. Integrated devices scaling rules.</p>
3	<p>Block 3. Integrated circuits with bipolar transistors</p> <p>3.1.- Circuits with BJT transistors. Device structure and operation principles. V-I characteristics. Operation modes. Small-signal model. Performance comparison between bipolar and MOS transistors. Bias circuits for BJTs. Resistor network. Current mirrors. Amplifiers with bipolar transistors. Single-stage amplifiers. Transistors interconnections. Differential amplifier.</p>
4	<p>Block 4.- Power conversion devices and circuits</p> <p>4.1.- Power devices. Ideal power switch. Power diodes. Power MOSFET. Insulated Gate Bipolar Transistor (IGBT).</p>

### 7. ASSESSMENT METHODS AND CRITERIA

Description	Type	Final Eval.	Reassessn	%
Assessment of the lab practices and reports	Laboratory evaluation	No	Yes	30,00
Final exam	Written exam	Yes	Yes	40,00
Work assignment and continuous assessment	Others	No	No	30,00
<b>TOTAL</b>				<b>100,00</b>
<b>Observations</b>				
Punctuality in the attendance to classes is requested for the students to be able to take the test linked to the continuous assessment integrated in the learning activities.				
<b>Observations for part-time students</b>				
Since 60% of the to total grading depends on the activities in the classroom and lab (continuous assessment and laboratory, not retrievable), the assessment criteria are the same for all students.				

### 8. BIBLIOGRAPHY AND TEACHING MATERIALS

#### BASIC

Sedra/Smith Microelectronic Circuits (6th edition). Oxford University Press. 2010

Behzad Razavi. Fundamentals of Microelectronics. 2nd Edition Wiley. 2013